# TH72036

#### 868/915MHz

#### FSK/ASK Transmitter

#### **Features**

- Fully integrated PLL-stabilized VCO
- Frequency range from 850 MHz to 930 MHz
- Single-ended RF output
- FSK through crystal pulling allows modulation from DC to 40 kbit/s
- High FSK deviation possible for wideband data transmission
- ASK achieved by on/off keying of internal
- power amplifier up to 40 kbit/s
- Wide power supply range from 1.95 V to 5.5 V
- Very low standby current
- Microcontroller clock output
- On-chip low voltage detector
- High over-all frequency accuracy
- FSK deviation and center frequency
- independently adjustable
- Adjustable output power range from
- -13 dBm to +9.5 dBm
- Adjustable current consumption from
- 2.5 mA to 20.1 mA
- Conforms to EN 300 220 and similar standards
- 10-pin quad flat no lead (QFN) package

# **Ordering information**

# Product CodeTemperature CodePackage CodeOption CodePacking Form CodeTH72036KLDCAA-000RETH72036KLDCAA-000TU

#### Legend:

Temperature Code:K for Temperature Range -40°C to 125°CPackage Code:LD for QFN doublePacking Form:RE for Reel, TU for TubeOrdering example:TH72036KLD-CAA-000-TU

# **General Description**

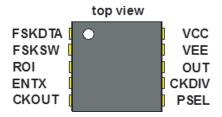
The TH72036 FSK/ASK transmitter IC is designed for applications in the European 868 MHz industrial-scientific-medical (ISM) band, according to the EN 300 220 telecommunications standard. It can also be used for any other system with carrier frequencies ranging from 850 MHz to 930 MHz (e.g. for applications in the US 902 to 928 MHz ISM band). The transmitter's carrier frequency f is determined by the frequency of the reference crystal f . The integrated PLL

The transmitter's carrier frequency  $f_c$  is determined by the frequency of the reference crystal  $f_{ref}$ . The integrated PLL synthesizer ensures that carrier frequencies, ranging from 850 MHz to 930 MHz, can be achieved. This is done by using a crystal with a reference frequency according to:  $f_{ref} = f_c/N$ , where N = 32 is the PLL feedback divider ratio. A clock signal with selectable frequency is provided. It can be used to drive a microcontroller.

## **Application Examples**

- Tire Pressure Monitoring System (TPMS)
- Remote Keyless Entry (RKE)
- Automatic Meter Reading (AMR)
- Alarm and security systems
- Garage door openers
- Home and building automation
- Low-power telemetry
- Wireless access control

## **Pin Description**









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#### TH72036 868/915MHz FSK/ASK Transmitter

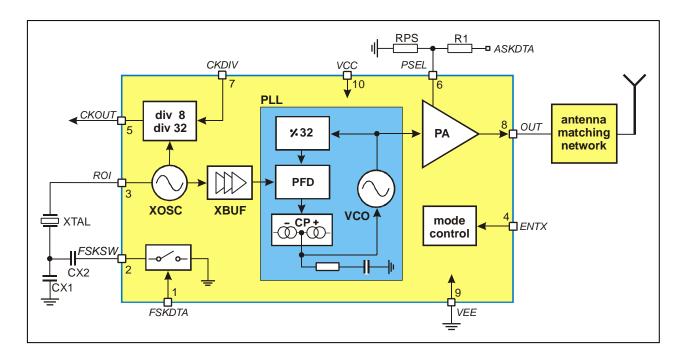


## **1. Theory of Operation**

#### 1.1. General

As depicted in Fig.1, the TH72036 transmitter consists of a fully integrated voltage-controlled oscillator (VCO), a divide-by-32 divider (div32), a phase-frequency detector (PFD) and a charge pump (CP). An internal loop filter determines the dynamic behavior of the PLL and suppresses reference spurious signals. A Colpitts crystal oscillator (XOSC) is used as the reference oscillator of a phase-locked loop (PLL) synthesizer. The VCO's output signal feeds the power amplifier (PA). The RF signal power  $P_{out}$  can be adjusted in four steps from  $P_{out} = -11$  dBm to +9.5 dBm, either by changing the value of resistor RPS or by varying the voltage  $V_{PS}$  at pin PSEL. The open-collector output (OUT) can be used either to directly drive a loop antenna or to be matched to a 500hm load. Bandgap biasing ensures stable operation of the IC at a power supply range of 1.95 V to 5.5 V.

#### 1.2. Block Diagram



*Fig. 1: Block diagram with external components* 

## **2. Functional Description**

#### 2.1. Crystal Oscillator

A Colpitts crystal oscillator with integrated functional capacitors is used as the reference oscillator for the PLL synthesizer. The equivalent input capacitance CRO offered by the crystal oscillator input pin ROI is about 18pF. The crystal oscillator is provided with an amplitude control loop in order to have a very stable frequency over the specified supply voltage and temperature range in combination with a short start-up time.



#### 2.2. FSK Modulation

FSK modulation can be achieved by pulling the crystal oscillator frequency. A CMOS-compatible data stream applied at the pin FSKDTA digitally modulates the XOSC via an integrated NMOS switch. Two external pulling capacitors CX1 and CX2 allow the FSK deviation  $\Delta f$  and the center frequency  $f_c$  to be adjusted independently. At FSKDTA = 0, CX2 is connected in parallel to CX1 leading to the low-frequency component of the FSK spectrum ( $f_{min}$ ); while at FSKDTA = 1, CX2 is deactivated and the XOSC is set to its high frequency  $f_{max}$ .

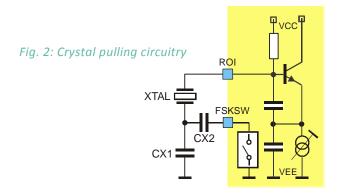
An external reference signal can be directly ACcoupled to the reference oscillator input pin ROI. Then the transmitter is used without a crystal. Now the reference signal sets the carrier frequency and may also contain the FSK (or FM) modulation.

#### 2.3. Crystal Pulling

A crystal is tuned by the manufacturer to the required oscillation frequency  $f_0$  at a given load capacitance CL and within the specified calibration tolerance. The only way to pull the oscillation frequency is to vary the effective load capacitance CL<sub>eff</sub> seen by the crystal.

Figure 3 shows the oscillation frequency of a crystal as a function of the effective load capacitance. This capacitance changes in accordance with the logic level of FSKDTA around the specified load capacitance. The figure illustrates the relationship between the external pulling capacitors and the frequency deviation.

It can also be seen that the pulling sensitivity increases with the reduction of CL. Therefore, applications with a high frequency deviation require a low load capacitance. For narrow band FSK applications, a higher load capacitance could be chosen in order to reduce the frequency drift caused by the tolerances of the chip and the external pulling capacitors.



FSKDTA	Description
0	$f_{min}\text{=}~f_{c}$ - $\Delta f$ (FSK switch is closed)
1	$f_{max}$ = $f_c$ + $\Delta f$ (FSK switch is open)

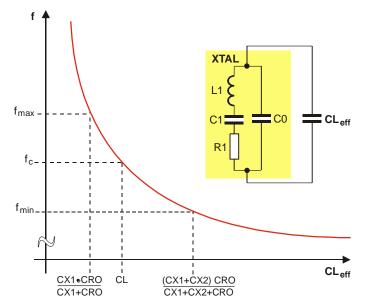


Fig. 3: Crystal pulling characteristic

For ASK applications CX2 can be omitted. Then CX1 has to be adjusted for center frequency.

#### TH72036 868/915MHz FSK/ASK Transmitter 2.4. ASK Modulation



The TH72036 can be ASK-modulated by applying data directly at pin PSEL. This turns the PA on and off which leads to an ASK signal at the output.

#### 2.5. Output Power Selection

The transmitter is provided with an output power selection feature. There are four predefined output power steps and one off-step accessible via the power selection pin PSEL. A digital power step adjustment was chosen because of its high accuracy and stability. The number of steps and the step sizes as well as the corresponding power levels are selected to cover a wide spectrum of different applications.

The implementation of the output power control logic is shown in figure 4. There are two matched current sources with an amount of about 8  $\mu$ A. One current source is directly applied to the PSEL pin. The other current source is used for the generation of reference voltages with a resistor ladder. These reference voltages are defining the thresholds between the power steps. The four comparators deliver thermometer-coded control signals depending on the voltage level at the pin PSEL. In order to have a certain amount of ripple tolerance in a noisy environment the comparators are provided with a little hysteresis of about 20 mV. With these control signals, weighted current sources of the power amplifier are switched on or off to set the desired output power level (Digitally Controlled Current Source). The LOCK, ASK signal and the output of the low voltage detector are gating this current source.

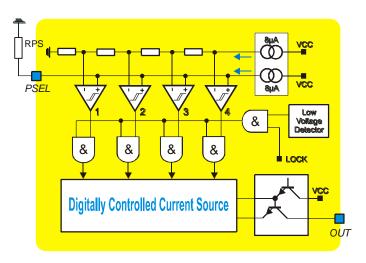


Fig. 4: Block diagram of output power control circuitry

There are two ways to select the desired output power step. First by applying a DC voltage at the pin PSEL, then this voltage directly selects the desired output power step. This kind of power selection can be used if the transmission power must be changed during operation. For a fixed-power application a resistor can be used which is connected from the PSEL pin to ground. The voltage drop across this resistor selects the desired output power level. For fixed-power applications at the highest power step this resistor can be omitted. The pin PSEL is in a high impedance state during the "TX standby" mode.

#### 2.6. Lock Detection

The lock detection circuitry turns on the power amplifier only after PLL lock. This prevents from unwanted emission of the transmitter if the PLL is unlocked.

#### 2.7. Low Voltage Detection

The supply voltage is sensed by a low voltage detect circuitry. The power amplifier is turned off if the supply voltage drops below a value of about 1.85 V. This is done in order to prevent unwanted emission of the transmitter if the supply voltage is too low.

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## 2.8. Mode Control Logic

The mode control logic allows two different modes of operation as listed in the following table. The mode control pin EN is pulled-down internally. This guarantees that the whole circuit is shut down if this pin is left floating.

EN	Mode	Description
0	TX standby	TX disabled
1	TX active CKOUT active	TX / CKOUT enabled

#### 2.9. Clock Output

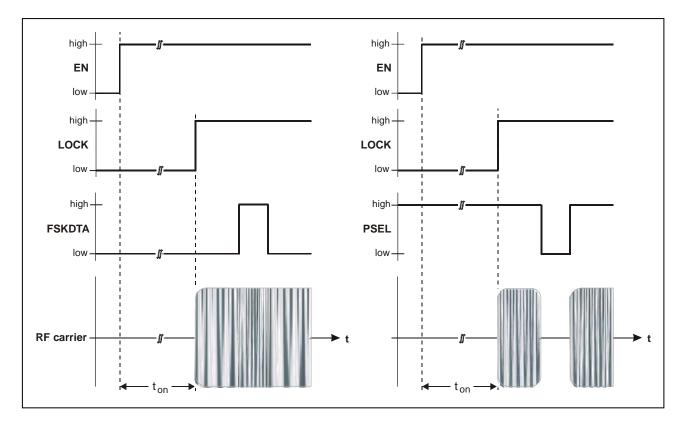
The clock output CKOUT is CMOS-compatible and can be used to drive a microcontroller. The frequency of the clock can be selected by the clock divider control signal CKDIV, according to the following table.

A capacitor at pin CKOUT can be used to control the clock voltage swing and the RF spurious emission.

CKDIV	Clock divider ratio	Clock frequency / f <sub>c</sub> =868.3MHz
0	8	3.39MHz
1	32	848kHz

## 2.10. Timing Diagrams

After enabling the transmitter by the EN signal, the power amplifier remains inactive for the time ton, the transmitter start-up time. The crystal oscillator starts oscillation and the PLL locks to the desired output frequency within the time duration ton. After successful PLL lock, the LOCK signal turns on the power amplifier, and then the RF carrier can be FSK or ASK modulated.







# **3. Pin Definition and Description**

Pin No.	Name	I/О Туре	Functional Schematic	Description
1	FSKDTA	input		FSK data input, CMOS compatible with internal pull-up circuit TX standby: no pull-up TX active: pull-up
2	FSKSW	analog I/O		XOSC FSK pulling pin, MOS switch
3	ROI	analog I/O		XOSC connection to XTAL, Colpitts type crystal oscillator
4	EN	input		mode control input, CMOS-compatible with internal pull-down circuit
5	СКОИТ	output		clock output, CMOS-compatible
6	PSEL	analog I/O		power select input, high- impedance comparator logic TX standby: I <sub>PSEL</sub> = 0 TX active: I <sub>PSEL</sub> = 8μA
7	CKDIV	input		clock divider control input, CMOS compatible with internal pull-down circuit TX standby: no pull-down TX active: pull-down
8	OUT	output		power amplifier output, open collector
9	VEE	ground		negative power supply
10	VCC	supply		positive power supply



# 4. Electrical Characteristics

#### 4.1. Absolute Maximum Ratings

Parameter	Symbol	Condition	Min	Max	Unit
Supply voltage	V <sub>CC</sub>		0	7.0	V
Input voltage	V <sub>IN</sub>		-0.3	V <sub>cc</sub> +0.3	V
Storage temperature	T <sub>STG</sub>		-65	150	°C
Junction temperature	TJ			150	°C
Thermal Resistance	$R_{thJA}$			49	K/W
Power dissipation	$P_{diss}$			0.12	W
Electrostatic discharge	V <sub>ESD</sub>	human body model (HBM) according to CDF-AEC-Q100- 002	±2.0		kV

## 4.2. Normal Operating Conditions

Parameter	Symbol	Condition	Min	Max	Unit
Supply voltage	V <sub>cc</sub>		1.95	5.5	V
Operating temperature	T <sub>A</sub>		-40	125	°C
Input low voltage CMOS	V <sub>IL</sub>	EN, FSKDTA		0.3*V <sub>cc</sub>	V
Input high voltage CMOS	V <sub>IH</sub>	EN, FSKDTA	0.7*V <sub>cc</sub>		V
XOSC frequency	$f_{ref}$	set by the crystal	26.6	29	MHz
VCO frequency	f <sub>c</sub>	$f_c = 32 \bullet f_{ref}$	850	930	MHz
Clock frequency	f <sub>CLK</sub>	CKDIV=0, $f_{CLK} = f_{ref} / 8$	3.3	3.6	MHz
		CKDIV=1, $f_{CLK} = f_{ref}/32$	831	906	kHz
FSK deviation	Δf	depending on CX1, CX2 and crystal parameters	±2.5	±40	kHz
FSK Data rate	R	NRZ		40	kbit/s
ASK Data rate	R	NRZ		40	kbit/s

## 4.3. Crystal Parameters

Parameter	Symbol	Condition	Min	Max	Unit
Crystal frequency	f <sub>0</sub>	fundamental mode, AT	26.6	29	MHz
Load capacitance	CL		10	15	рF
Static capacitance	C <sub>0</sub>			7	рF
Series resistance	R <sub>1</sub>			50	Ω
Spurious response	a <sub>spur</sub>	only required for FSK		-10	dB



#### 4.4. DC Characteristics

all parameters under normal operating conditions, unless otherwise stated;

typical values at  $T_A$  = 23 °C and  $V_{CC}$  = 3 V

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Operating Currents						
Standby current	I <sub>SBY</sub>	EN=0, T <sub>A</sub> =85°C		0.2	200	nA
	.281	EN=0, T <sub>A</sub> =125°C			4	μΑ
Supply current in power step 0	I <sub>CC0</sub>	EN=1	2.5	4.3	7.4	mA
Supply current in power step 1	I <sub>CC1</sub>	EN=1	3.5	5.5	9.4	mA
Supply current in power step 2	I <sub>CC2</sub>	EN=1	4.5	6.8	11.1	mA
Supply current in power step 3	I <sub>CC3</sub>	EN=1	6.2	9.0	13.8	mA
Supply current in power step 4	I <sub>CC4</sub>	EN=1	9.4	13.8	20.1	mA
Digital Pin Characteristics						
Input low voltage CMOS	V <sub>IL</sub>	EN, FSKDTA	-0.3		0.3*V <sub>cc</sub>	V
Input high voltage CMOS	V <sub>IH</sub>	EN, FSKDTA	0.7*V <sub>cc</sub>		V <sub>cc</sub> +0.3	V
Pull down current, EN	I <sub>PDEN</sub>	EN=1	0.2	4.0	40	μΑ
Low level input current, EN	I <sub>INLEN</sub>	EN=0			0.02	μΑ
High level input current, FSKDTA	I <sub>INHDTA</sub>	FSKDTA=1			0.02	μΑ
Pull up current FSKDTA active mode	I <sub>PUDTAa</sub>	FSKDTA=0, EN=1	0.1	1.5	12	μΑ
Pull up current FSK standby mode	I <sub>PUDTAs</sub>	FSKDTA=0, EN=0			0.02	μΑ
Low level input current CKDIV	I <sub>INLCKDIV</sub>	CKDIV=0			0.02	μΑ
Pull-down current CKDIV active mode	I <sub>PDCKDIVa</sub>	CKDIV=1, EN=1	0.1	1.5	12	μΑ
Pull-down current CKDIV standby mode	I <sub>PDCKDIVs</sub>	CKDIV=1, EN=0			0.02	μΑ
FSK Switch Resistance						
MOS switch On resistance	R <sub>ON</sub>	FSKDTA=0, EN=1		20	70	Ω
MOS switch Off resistance	R <sub>OFF</sub>	FSKDTA=1, EN=1	1			MΩ
Power Select Characteristics		•				
Power select current	I <sub>PSEL</sub>	EN=1	7.0	8.6	9.9	μΑ
Power select voltage step 0	V <sub>PS0</sub>	EN=1			0.035	V
Power select voltage step 1	V <sub>PS1</sub>	EN=1	0.14		0.24	V
Power select voltage step 2	V <sub>PS2</sub>	EN=1	0.37		0.60	V
Power select voltage step 3	V <sub>PS3</sub>	EN=1	0.78		1.29	V
Power select voltage step 4	$V_{PS4}$	EN=1	1.55			V
Low Voltage Detection Character	ristic					
Low voltage detect threshold	V <sub>LVD</sub>	EN=1	1.75	1.85	1.95	V

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#### 4.5. AC Characteristics

all parameters under normal operating conditions, unless otherwise stated;

typical values at  $T_{\rm A}$  = 23 °C and  $V_{\rm CC}$  = 3 V; test circuit shown in Fig. 6,  $f_{\rm c}$  = 868.3MHz

Parameter	Symbol	Condition	Min	Тур	Max	Unit
CW Spectrum Characteristics						
Output power in step 0 (Isolation in off-state)	P <sub>off</sub>	EN=1			-70	dBm
Output power in step 1	P <sub>1</sub>	EN=1	-13	-12	-11 1)	dBm
Output power in step 2	P <sub>2</sub>	EN=1	-4	-3	-2 <sup>1)</sup>	dBm
Output power in step 3	P <sub>3</sub>	EN=1	1	2.5	3.5 <sup>1)</sup>	dBm
Output power in step 4	P <sub>4</sub>	EN=1	4	7.5	9.5 <sup>1)</sup>	dBm
Phase noise	L(f <sub>m</sub> )	@ 200kHz offset		-87	-82	dBc/Hz
Spurious emissions according to EN 300 220-1 (2000.09) table 13	P <sub>spur</sub>	47MHz< f <74MHz 87.5MHz< f <118MHz 174MHz< f <230MHz 470MHz< f <862MHz B=100kHz			-54	dBm
		f < 1GHz, B=100kHz			-36	dBm
		f > 1GHz, B=1MHz			-30	dBm
Clock output Characteristics						
Output low voltage CMOS	V <sub>OL</sub>	depending on capacitor			0.3*V <sub>CC</sub>	V
Output high voltage CMOS	V <sub>OH</sub>	CCK and CKDIV	0.7*V <sub>CC</sub>			V
Start-up Parameters						
Start-up time	t <sub>on</sub>	from standby to transmit mode		0.6	1	ms
Frequency Stability						
Frequency stability vs. supply voltage	df <sub>vcc</sub>				±3	ppm
Frequency stability vs. temperature	df <sub>TA</sub>	crystal at constant temperature	-		±10	ppm
Frequency stability vs. variation range of $C_{RO}$	df <sub>CRO</sub>				±20	ppm

1) output matching network tuned for 5V supply

#### TH72036 868/915MHz FSK/ASK Transmitter 4.6. AC Characteristics



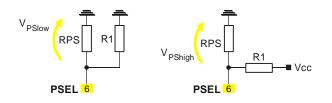
Power step	0	1	2	3	4
RPS / kΩ	< 3	22	56	120	not connected

#### 4.7. Output Power Steps – ASK Mode

typical values at  $T_{\text{A}}$  = 23 °C and  $V_{\text{CC}}$  = 3 V; test circuit shown in Fig. 6

Power step	1	2	3	4
RPS / kΩ	2.4	2.8	3.5	not connected
R1 / kΩ	36	14	7	0

 $V_{PSlow}$  = voltage across RPS if ASK\_DTA at 0V  $V_{PShigh}$  = voltage across RPS if ASK\_DTA at Vcc



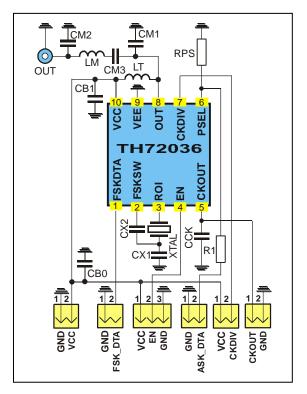
If the transmitter is operated at any supply voltage  $V_{cc}$ , the values for R1 and RPS can be calculated as follows:

$$R_1 = \frac{V_{CC} \cdot V_{PSlow}}{I_{PSEL} \cdot V_{PShigh}}$$

$$R_{PS} = R_1 \frac{V_{PShigh}}{V_{CC} - V_{PShigh}}$$



## 5. Test Circuit





## 5.1. Test circuit component list to Fig. 6

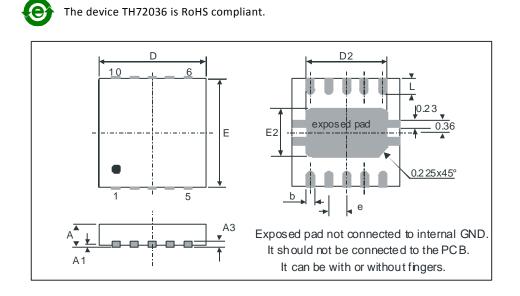
Part	Size	Value @ 868.3 MHz	Value @ 915 MHz	Tolerance	Description	
CM1	0805	1.8 pF	2.2 pF	±5%	impedance matching capacitor	
CM2	0805	5.6 pF	5.6 pF	±5%	impedance matching capacitor	
CM3	0805	68 pF	68 pF	±5%	impedance matching capacitor	
LM	0805	12 nH	10 nH	±5%	impedance matching inductor, note 2	
LT	0805	15 nH	10 nH	±5%	output tank inductor, note 2	
CX1_ <sub>FSK</sub>	0805	22 pF	22 pF	±5%	XOSC FSK capacitor ( $\Delta f = \pm 20 \text{ kHz}$ ), note 1	
CX1_ASK	0805	27 pF	27 pF	±5%	XOSC ASK capacitor, trimmed to f <sub>c</sub> , note 1	
CX2	0805	12 pF	12 pF	±5%	XOSC capacitor ( $\Delta f = \pm 20 \text{ kHz}$ ), note 1 only needed for FSK	
ССК	0805	15 pF / 180 pF		±5%	clock spur suppression capacitor, CKDIV 0 / 1	
RPS	0805	see section 4.6		±5%	FSK or CW mode power-select resistor	
R1		see section 4.7			ASK power-select resistor, not used at FSK	
CB0	0805	220 nF		±20%	de-coupling capacitor	
CB1	0805	330 pF		±10%	de-coupling capacitor	
XTAL	SMD 6x3.5	27.13438 MHz	28.59375 MHz	$ \begin{array}{ll} \pm 30 \mbox{ppm calibr.} & fundamental wave crystal, \\ \pm 30 \mbox{ppm temp.} & CL = 12 \mbox{ pF, C0, max = 7 \mbox{ pF, R1 = 40 } \Omega \end{array} $		

**Note 1:** value depending on crystal parameters

Note 2: for high-power applications high-Q wire-wound inductors should be used



## 6. Package Description



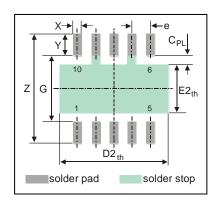
#### Fig. 7: 10L QFN 3x3 Dual

all Dimensions in mm										
	D	E	D2	E2	Α	A1	A3	L	е	b
min	2.85	2.85	2.23	1.49	0.80	0	0.20	0.3	0.50	0.18
max	3.15	3.15	2.48	1.74	1.00	0.05	0.20	0.5	0.50	0.30
all Dimensions in inch										
min	0.112	0.112	0.0878	0.051	0.0315	0	0.0079	0.0118	0.0197	0.0071
max	0.124	0.124	0.0976	0.055	0.0393	0.002	0.0079	0.0197	0.0197	0.0118

## 6.1. Soldering Information

 The device TH72036 is qualified for MSL1 with soldering peak temperature 260 deg C according to JEDEC J-STD-20

#### 6.2. Recommended PCB Footprints



all Dimensions in mm								
	Z	G	D2 <sub>th</sub>	E2 <sub>th</sub>	X	Y	C <sub>PL</sub>	е
min	3.55	1.9	3.2	1.3	0.25	0.7	0.3	0.5
max	3.90	2.3	3.6	1.7	0.30	1.0	0.5	0.5
all Di	all Dimensions in inch							
min	0.1398	0.0748	0.1260	0.0512	0.0098	0.0276	0.0591	0.0197
max	0.1535	0.0906	0.1417	0.0669	0.0118	0.0394	0.0197	0.0197

#### Fig. 8: PCB land pattern style



# 7. Standard information regarding manufacturability of Melexis products with different soldering processes

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to following test methods:

#### Reflow Soldering SMD's (Surface Mount Devices)

- IPC/JEDEC J-STD-020 Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices (classification reflow profiles according to table 5-2)
- EIA/JEDEC JESD22-A113
  Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing (reflow profiles according to table 2)

#### Wave Soldering SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

- EN60749-20
- Resistance of plastic- encapsulated SMD's to combined effect of moisture and soldering heat
- EIA/JEDEC JESD22-B106 and EN60749-15 Resistance to soldering temperature for through-hole mounted devices

#### Iron Soldering THD's (<u>Through Hole Devices</u>)

• EN60749-15 Resistance to soldering temperature for through-hole mounted devices

#### Solderability SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

• EIA/JEDEC JESD22-B102 and EN60749-21 Solderability

For all soldering technologies deviating from above mentioned standard conditions (regarding peak temperature, temperature gradient, temperature profile etc) additional classification and qualification tests have to be agreed upon with Melexis.

The application of Wave Soldering for SMD's is allowed only after consulting Melexis regarding assurance of adhesive strength between device and board.

Melexis is contributing to global environmental conservation by promoting **lead free** solutions. For more information on qualifications of **RoHS** compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website: <u>http://www.melexis.com/quality.aspx</u>

## 8. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.



#### 9. Contact

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